## RT3AMMAM1

Composite Transistor
For Low Frequency Amplify Application
Silicon Pnp Epitaxial Type

## DESCRIPTION

RT3AMMAM1 is a composite transistor built with two ISA1235A chips in SC-88 package.

## **FEATURE**

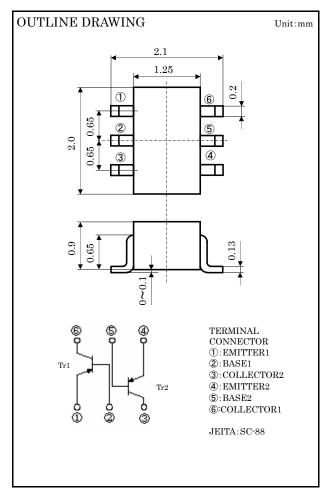
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Each transistor elements are independent.

Mini package for easy mounting

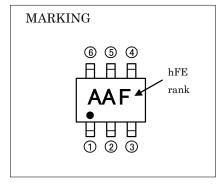
## APPLICATION

For low frequency amplify application



## MAXIMUM RATING (Ta=25°C) (The characteristics apply to both Tr1 and Tr2.)

SYMBOL	PARAMETER	RATING	UNIT	
Vcbo	Collector to Base voltage	-60	V	
Vebo	Emitter to Base voltage	-6	V	
$V_{\rm CEO}$	Collector to Emitter voltage	-50	V	
Ic	Collector current	-200	mA	
Pc	Collector dissipation (Total,Ta=25°C)	150	mW	
Tj	Junction temperature	+125	°C	
$T_{\mathrm{stg}}$	Storage temperature	-55~+125	°C	



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# ELECTRICAL CHARACTERISTICS (Ta=25°C) (The characteristics apply to both Tr1 and Tr2.)

Symbol	Parameter	Test conditions	Limits			TT. 14
		lest conditions	Min	Тур	Max	Unit
V(BR)CEO	Collector to Emitter break down voltage	I <sub>C</sub> =100 μ A,R <sub>BE</sub> =∞	-50	-	-	V
ICBO	Collector cut off current	V <sub>CB</sub> =-60V,I <sub>E</sub> =0	-	-	-0.1	μΑ
IEBO	Emitter cut off current	$V_{\mathrm{EB}}$ =-6 $V_{\mathrm{IC}}$ =0	-	-	-0.1	μΑ
hFE*	DC forward current gain	V <sub>CE</sub> =-6V,I <sub>C</sub> =-1mA	150	-	500	-
hFE	DC forward current gain	V <sub>CE</sub> =-6V,I <sub>C</sub> =-0.1mA	90	-	-	-
VCE(sat)	Collector to Emitter saturation voltage	Ic=-100mA,I <sub>B</sub> =-10mA	-	-	-0.3	V
fT	Gain band width product	V <sub>CE</sub> =-6V,I <sub>E</sub> =10mA	-	200	-	MHz
Cob	Collector output capacitance	V <sub>CB</sub> =-6V,I <sub>E</sub> =0,f=1MH <sub>Z</sub>	-	4.0	-	pF
NF	Noise figure	$V_{CE}$ =6 $V_{,IE}$ =0.3 $mA_{,f}$ =100 $H_{Z}$ , $R_{G}$ =10 $k\Omega$	-	-	20	dB

 $oldsymbol{*}$ : It shows hfe classification in right table.

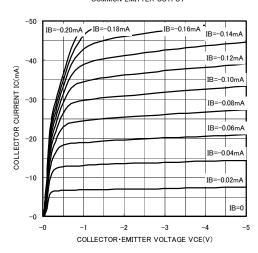
item	E	F
hre	150~300	250~500

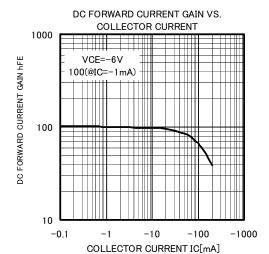
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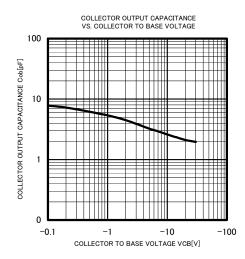
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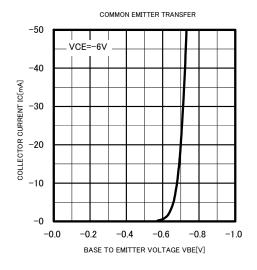
## TYPICAL CHARACTERISTICS (Tr1, Tr2)

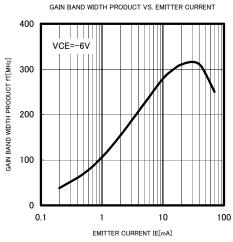
#### COMMON EMITTER OUTPUT













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